

High Voltage Power MOSFET

IXTH1N250

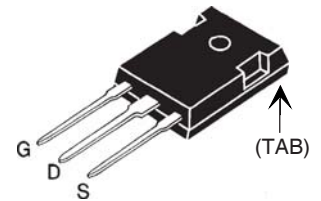
$V_{DSS} = 2500V$
 $I_{D25} = 1.5A$
 $R_{DS(on)} \leq 40\Omega$

N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	2500	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	2500	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	1.5	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	6	A
P_D	$T_C = 25^\circ C$	250	W
T_J		- 55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		- 55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10s	260	$^\circ C$
M_d	Mounting torque	1.13 / 10	Nm/lb.in.
Weight		6	g

TO-247 AD (IXTH)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- International standard package
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	2500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ C$		25	25 μA μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			40 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 50\text{V}$, $I_D = 0.5\text{A}$, Note 1	1.0	1.8	mS
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		1660	pF
C_{oss}			77	pF
C_{rss}			23	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 1\text{A}$ $R_G = 5\Omega$ (External)		69	ns
t_r			25	ns
$t_{d(off)}$			132	ns
t_f			39	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 600\text{V}$, $I_D = 0.5\text{A}$		41	nC
Q_{gs}			8	nC
Q_{gd}			16	nC
R_{thJC}			0.50	$^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

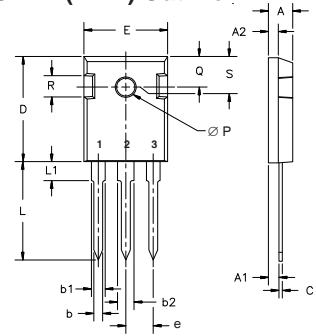
Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			1.5 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			6 A
V_{SD}	$I_F = 1\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 1\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 200\text{V}$		2.5	μs

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

2: Additional provisions for lead to lead voltage isolation are required at $V_{DS} > 1200\text{V}$.

TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

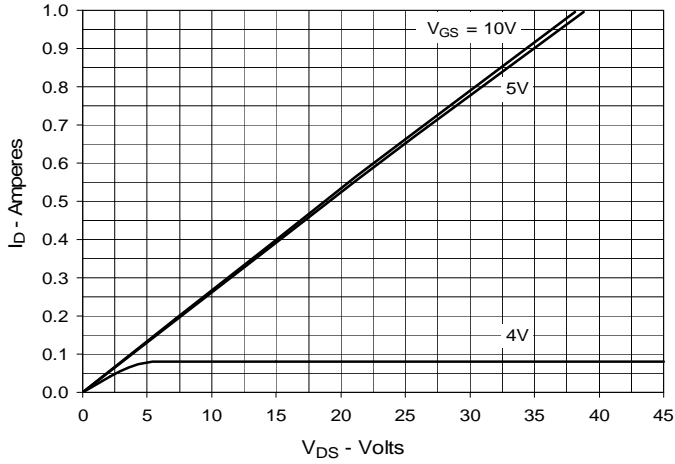
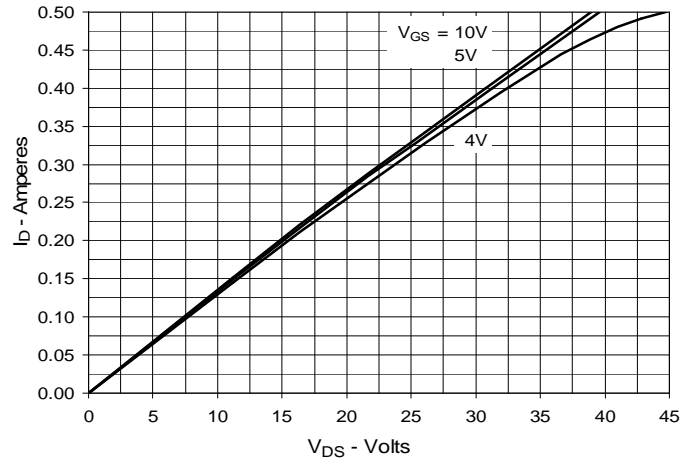
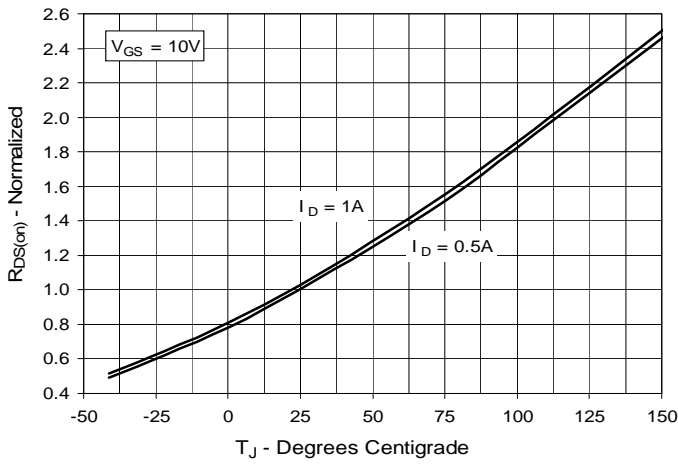
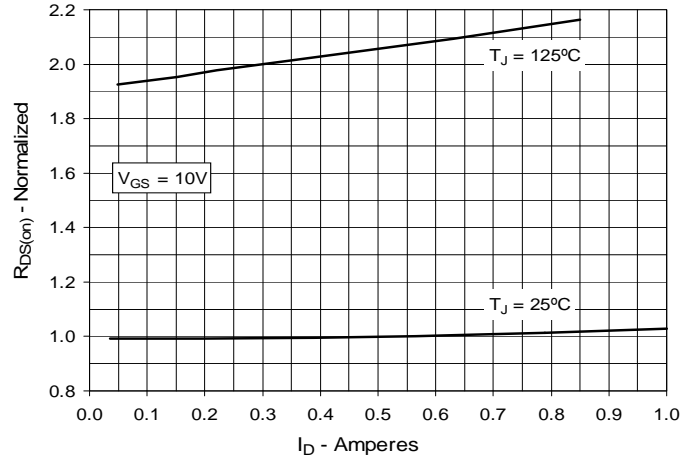
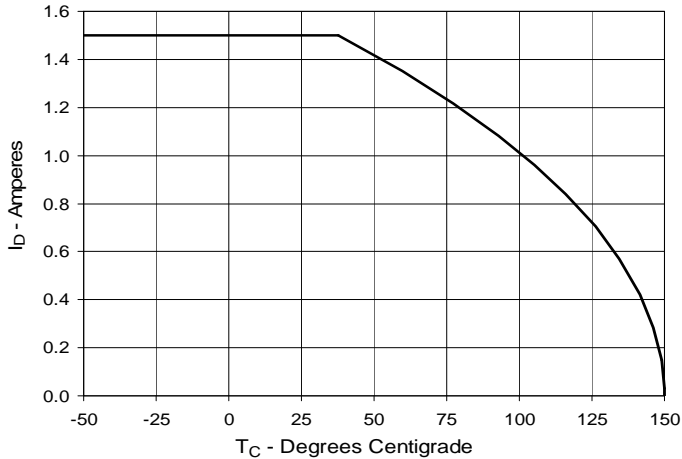
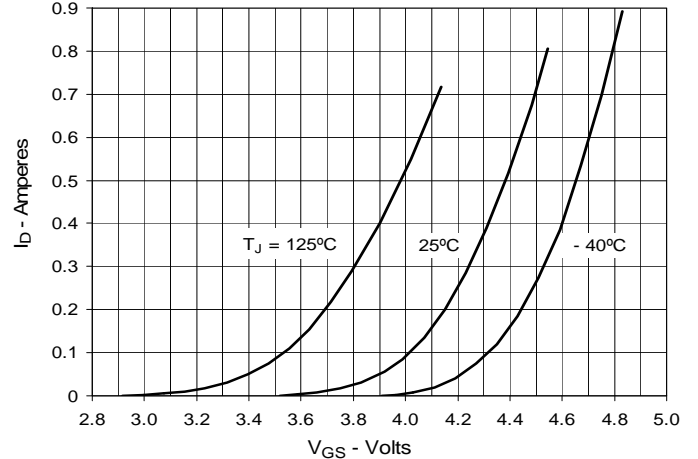
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value
vs. Junction Temperature**

**Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value
vs. Drain Current**

**Fig. 5. Maximum Drain Current vs.
Case Temperature**

Fig. 6. Input Admittance


Fig. 7. Transconductance

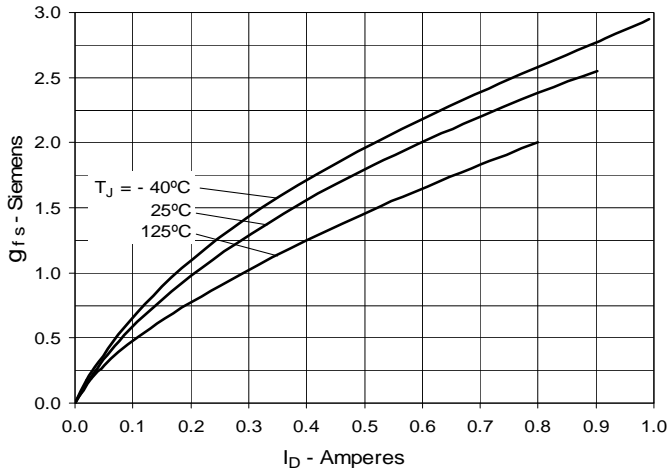


Fig. 8. Forward Voltage Drop of Intrinsic Diode

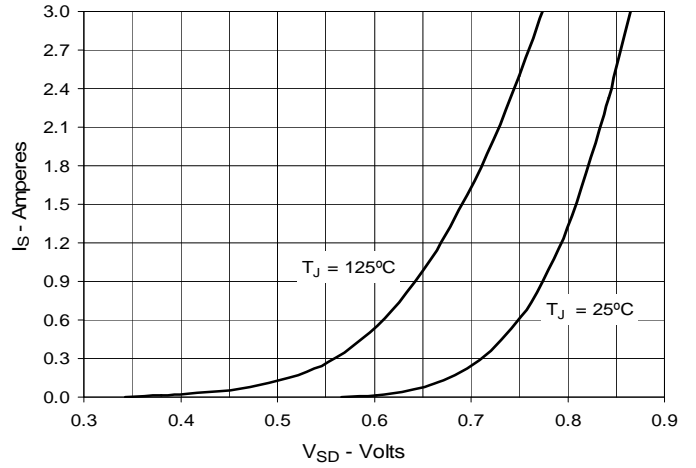


Fig. 9. Gate Charge

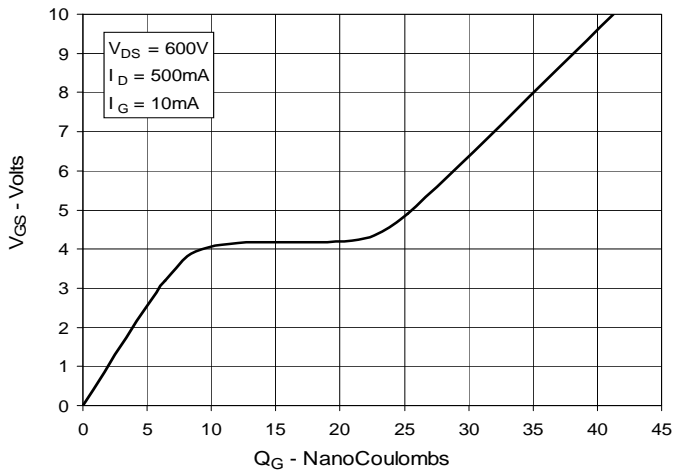


Fig. 10. Capacitance

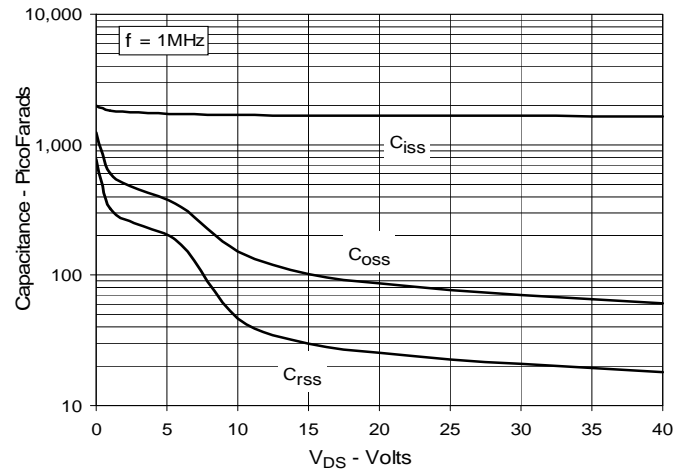


Fig. 11. Maximum Transient Thermal Impedance

